

## IN THE CLAIMS

1 (Currently Amended). A method comprising:  
developing a patterned photoresist;  
applying a plasticizer in a supercritical fluid to the surface of said patterned photoresist ~~to decrease line edge roughness after developing the photoresist~~; and  
reflowing the photoresist after applying the plasticizer.

Claim 2 (Canceled).

3 (Currently Amended). The method of claim 1 ~~-2-~~ including applying the plasticizer in a supercritical carbon dioxide fluid.

Claims 4 and 5 (Canceled).

6 (Original). The method of claim 1 including applying the plasticizer with the develop rinse.

7 (Original). The method of claim 1 including applying a plasticizer that improves the etch resistance of the photoresist.

8 (Original). The method of claim 1 wherein applying a plasticizer includes diffusing a plasticizer into the photoresist.

9 (Original). The method of claim 8 including diffusing a plasticizer in a vapor phase into the photoresist.

10 (Original). The method of claim 1 including controlling the amount of reflow by volatilizing the plasticizer during reflow.

11 (Original). The method of claim 1 including applying the plasticizer in liquid carbon dioxide.

12 (Original). The method of claim 1 including controlling the amount of reflow by cooling the photoresist.

Claims 13-27 (Canceled).